

MOS FIELD EFFECT TRANSISTOR 2SK3918

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3918 is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, and designed for low voltage high current applications such as DC/DC converter with synchronous rectifier.

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3918	TO-251 (MP-3)
2SK3918-ZK	TO-252 (MP-3ZK)

FEATURES

- Low on-state resistance
 R_{DS(on)1} = 7.5 mΩ MAX. (V_{GS} = 10 V, I_D = 24 A)
- Low Ciss: Ciss = 1300 pF TYP.
- 5 V drive available

(TO-251)



(TO-252)



ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vss = 0 V)	Voss	25	V
Gate to Source Voltage (Vps = 0 V)	Vgss	±20	V
Drain Current (DC) (Tc = 25°C)	ID(DC)	±48	Α
Drain Current (pulse) Note1	I _{D(pulse)}	±192	Α
Total Power Dissipation (Tc = 25°C)	P _{T1}	29	W
Total Power Dissipation	P _{T2}	1.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C
Single Avalanche Current Note2	las	22	Α
Single Avalanche Energy Note2	Eas	48	mJ

Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Starting T_{ch} = 25°C, V_{DD} = 12.5 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V

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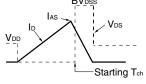
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERICTICS	CVMDOL	TEST CONDITIONS	NAINI	TVD	MAX	LINUT
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 25 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	V _{GS} = ±20 V, V _{DS} = 0 V			±100	nA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	2.0	2.5	3.0	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10 V, I _D = 12 A	6	12		S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = 10 V, I _D = 24 A		5.9	7.5	mΩ
	RDS(on)2	V _{GS} = 5.0 V, I _D = 12 A		11	22.2	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V		1300		pF
Output Capacitance	Coss	V _{GS} = 0 V		310		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		220		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 12.5 V, I _D = 24 A		13		ns
Rise Time	t r	V _{GS} = 10 V		14		ns
Turn-off Delay Time	t _{d(off)}	$R_G = 10 \Omega$		38		ns
Fall Time	tf			14		ns
Total Gate Charge	Q _G	V _{DD} = 20 V		28		nC
Gate to Source Charge	Qgs	V _{GS} = 10 V		5		nC
Gate to Drain Charge	Q _{GD}	I _D = 48 A		10		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 48 A, V _{GS} = 0 V		0.98		V
Reverse Recovery Time	trr	I _F = 48 A, V _{GS} = 0 V		27		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		15		nC

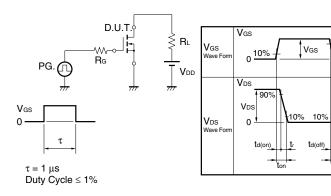
Note Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = 20 \rightarrow 0 \text{ V}$ $PG. \bigcirc PG. \bigcirc PG.$



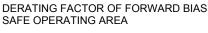
TEST CIRCUIT 2 SWITCHING TIME

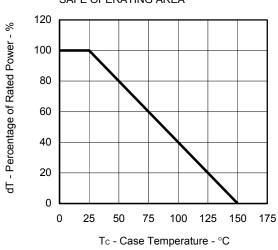


TEST CIRCUIT 3 GATE CHARGE

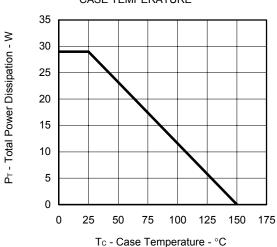


TYPICAL CHARACTERISTICS (TA = 25°C)

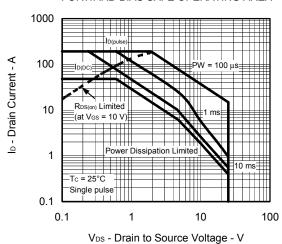


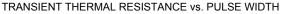


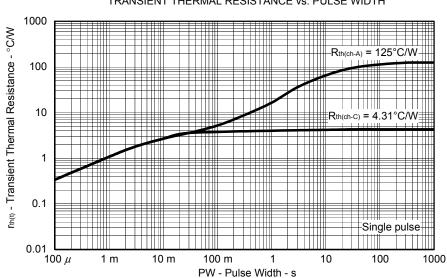
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



FORWARD BIAS SAFE OPERATING AREA







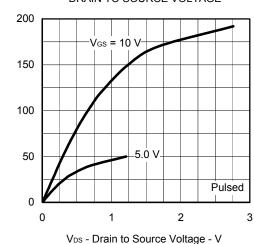
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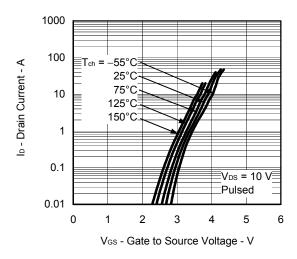
Ip - Drain Current - A

VGS(off) - Gate Cut-off Voltage - V

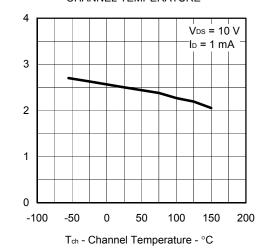
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



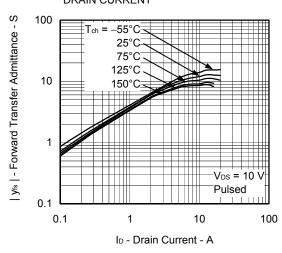
FORWARD TRANSFER CHARACTERISTICS



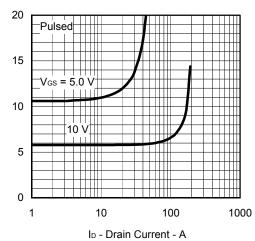
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



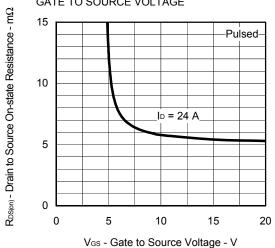
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. **DRAIN CURRENT**



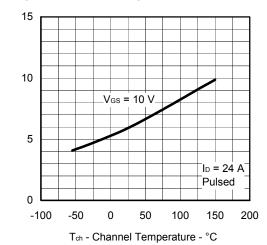
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



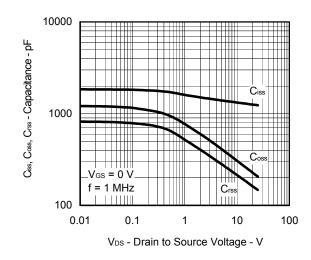
RDS(on) - Drain to Source On-state Resistance - m\Omega

RDS(on) - Drain to Source On-state Resistance - m\Omega

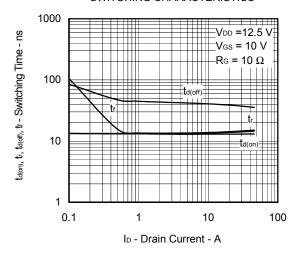
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



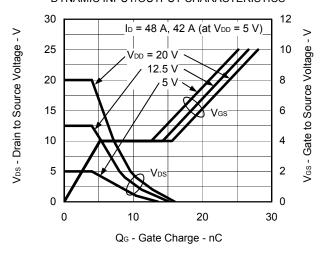
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



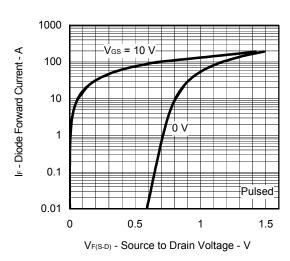
SWITCHING CHARACTERISTICS



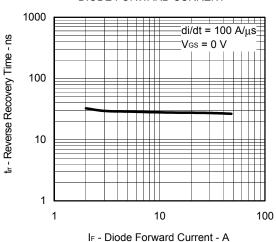
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



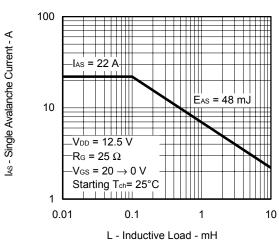
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



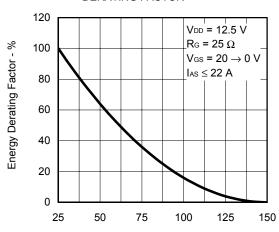
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



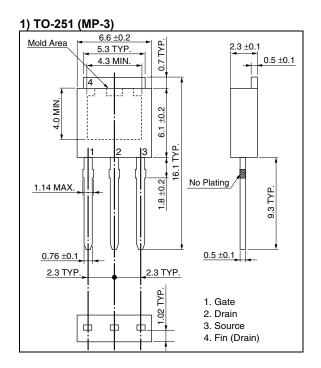
SINGLE AVALANCHE ENERGY DERATING FACTOR

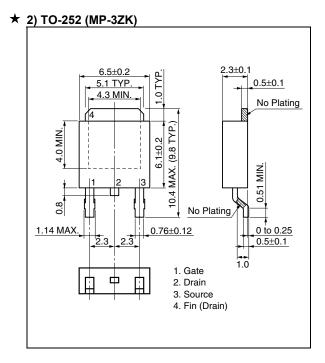


Starting Tch - Starting Channel Temperature - °C

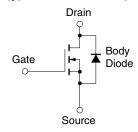


PACKAGE DRAWINGS (Unit: mm)





EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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